Erratum

The following is a correction to the caption of Fig. 5 on page 380 of the paper, "Monolithic integration of III-V optical interconnects on Si using SiGe virtual substrates" by V. K. Yang, M. E. Groenert, G. Taraschi, C. W. Leitz, A. J. Pitera, M. T. Currie, Z. Cheng and E. A. Fitzgerald in Volume 13, Issue 7, July 2002 of the *Journal of Materials Science: Materials in Electronics*.

Figure 5 Effect of geometry on detector response to LED emission. Detector output current to LED current ratio is plotted on the y-axis for both (a) and (b). (a) Shows the effect of waveguide length on the ratio. As the waveguide length increases, the output-to-input ratio decreases. The signal received from the detector connected to a 1 cm waveguide is smaller than the noise level of 1 nA. (b) Shows the effect of Y junction angle on the ratio. As the junction angle increases, the output-to-input ratio also decreases.